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| APPLICATION NO. | FILING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO | |
|---|---------------|----------------------|-------------------------|-----------------|--|
| 09/610,217 | 07/05/2000 | Shunpei Yamazaki | SEL 192 | 4725 | |
| 75 | 90 08/22/2002 | | | | |
| Cook Alex McFarron Manzo Cummings & Mehler Ltd 200 West Adams Street Suite 2850 | | | EXAMINER | | |
| | | | BOOTH, RICHARD A | | |
| Chicago, IL 60 | 0606 | | ART UNIT | PAPER NUMBER | |
| | | | 2812 | () | |
| | | | DATE MAILED: 08/22/2002 | 13 | |

Please find below and/or attached an Office communication concerning this application or proceeding.

| | | Application No. | Applicant(s) | |
|---|---|--|---|---------------|
| | | 09/610,217 | YAMAZAKI ET AL. | 1/ |
| · Office Action Summa | ry | Examiner | Art Unit | |
| | | Richard A. Booth | 2812 | |
| The MAILING DATE of this cor Period for Reply | mmunication app | ears on the cover she | eet with the correspondence add | iress |
| A SHORTENED STATUTORY PERI THE MAILING DATE OF THIS COM. Extensions of time may be wailable under the pro- after SIX (8) MONTHS from the mailing date of the if the period of reply specified above is less than i. If NO period for reply sapecified above, the maxi- port of the properties of the properties of the maxi- port of the properties of the properties of the pro- ter of the properties of the pro- ter of the properties of the pro- cess of the properties of the pro- ter of the protect of the pro- ter of the pro- ter of the protect of the protect of the pro- ter of the protect of the protect of the protect of the protect of the pro- ter of the protect of the | MUNICATION. ovisions of 37 CFR 1.13 iis communication. thirty (30) days, a reply imum statutory period w for reply will, by statute, nonths after the mailing | 6(a). In no event, however, r within the statutory minimum ill apply and will expire SIX (6 cause the application to become | may a reply be timely filed of thirty (30) days will be considered timely.) MONTHS from the mailing date of this corme ABANDONEO (35 U.S.C. § 133). | nmunication. |
| 1) Responsive to communication | n(s) filed on 28 N | lav 2002 . | | |
| 2a)☐ This action is FINAL . | | s action is non-final. | | |
| · - | ndition for allowa | nce except for forma | I matters, prosecution as to the | merits is |
| Disposition of Claims | practice under i | -x parte Quayle, 193 | 3 C.D. 11, 433 C.G. 213. | |
| 4)⊠ Claim(s) 1-52 is/are pending in | n the application. | | | |
| 4a) Of the above claim(s) 1-28 | | | sideration. | |
| 5) Claim(s) is/are allowed. | | | | |
| 6)⊠ Claim(s) 29-33 is/are rejected. | | | | |
| 7) Claim(s) is/are objected | I to. | | | |
| 8) Claim(s) are subject to r | restriction and/or | election requiremen | t. | * |
| Application Papers | | | | |
| 9)☐ The specification is objected to | by the Examiner | | | |
| 10) The drawing(s) filed on is | s/are: a)□ accep | ted or b) Objected to | by the Examiner. | |
| Applicant may not request that a | | | • | |
| 11) The proposed drawing correction | | | I disapproved by the Examine | r. |
| If approved, corrected drawings | | | | |
| 12) The oath or declaration is object | • | aminer. | | |
| Priority under 35 U.S.C. §§ 119 and 12 | | | | |
| 13) Acknowledgment is made of a | | priority under 35 U.S | S.C. § 119(a)-(d) or (f). | |
| a) All b) Some * c) None | | | | |
| 1. Certified copies of the pr | - | | | |
| 2. Certified copies of the pr | | | | |
| Copies of the certified co- application from the See the attached detailed Office | International Bur | eau (PCT Rule 17.2) | | itage |
| 14) Acknowledgment is made of a cl | laim for domestic | priority under 35 U. | S.C. § 119(e) (to a provisional | application). |
| a) ☐ The translation of the foreigns a) ☐ Acknowledgment is made of a c | | | | |
| Attachment(s) | ioi doillean | s pricing under 50 0. | 5.5. 33 120 dilator 121. | |
| Notice of References Cited (PTO-892) | | 4) 🗍 Inte | rview Summary (PTO-413) Paper No(s | i) |
| Notice of Natiserences Cited (F10-032) Notice of Draftsperson's Patent Drawing Ref Notice of Draftsperson's Patent Drawing Ref Notice of Natiserences Cited (F10-032) Notice of Natiserences Cited (F10-032) Notice of Natiserences Cited (F10-032) | | 5) 🔲 Noti | ce of Informal Patent Application (PTO | |
| S. Patent and Trademark Office PTO-326 (Rev. 04-01) | Office Act | tion Summary | Part of F | aper No. 13 |

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DETAILED ACTION

El ction/Restrictions

Applicant's election of the second species in Paper No. 12 is acknowledged.

Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 29-33 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

In all of the claims of record, the use of the phrase "island-like" renders the claims indefinite because the addition of a word such as type or like to an otherwise definite expression renders the term indefinite.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

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Claims 29, 31, and 33 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ohtani et al., U.S. Patent 5,643,826 in view of Fukuda et al., U.S. Patent 6.096.585.

Ohtani shows the invention substantially as claimed including a pixel TFT disposed in a pixel unit comprising the steps of: forming an underlying film 202 over the substrate 201; forming an island-like semiconductor film 208 over said underlying film; forming n-type source and drain regions (212,213) for said pixel TFT; forming a protective insulating film 211 or 214 formed of an inorganic insulating material above the pixel TFT; forming an inter-layer insulation film 215 formed of an organic insulating material in close contact with said protective insulating film; and forming on said inter-layer insulating film a pixel electrode 216 having a light reflective surface and connected to said pixel TFT (see figs. 10A-10F and col. 11-line 64 to col. 13-line 55).

Ohtani lacks anticipation of forming both peripheral and pixel TFTs (although this is alluded to at col. 1-lines 13-19) using the steps of: forming n type impurity regions having a first concentration, for forming LDD regions of said n channel type TFT of said driving circuit and said pixel TFT in selected regions of said island-like semiconductor layers; forming n type impurity regions having a second concentration, for forming source regions or drain regions outside said n type impurity regions having the first concentration; and forming a p type impurity region having a third concentration, for forming a source region or a drain region of said p channel TFT of said driving circuit in a selected region of said island-like semiconductor layers.

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Fukuda et al. discloses forming both peripheral and pixel TFTs with island-like semiconductor films 72 by forming n-type impurity regions having a first concentration (see fig. 7B), for forming LDD regions of said n channel type TFT of said n channel type TFT of said driving circuit and said pixel TFT in selected regions of said island-like semiconductor layer, forming n type impurity having a second concentration (see Fig. 7G) for forming source or drain regions (91c,72c, for example) outside said n-type regions having the first concentration; and forming a p type impurity region (see Fig. 7C) having a third concentration, for forming a source region or a drain region of said p channel TFT of said driving circuit in a selected region of said island-like semiconductor layer (see Figs. 7A-7H and col. 7-lines 5-51). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the reference of Ohtani with the peripheral and pixel formation disclosed by Fukuda et al. because this provides a beneficial structure for both the pixel and driving portions while reducing the number of processing steps.

With respect to claim 31, note that the gate electrode material 211 in Ohtani et al. is aluminum which is both heat resistant and of low conductivity as defined by these broad terms. Regarding claim 33, note that Ohtani et al. suggests the use of the invention in active matrix liquid crystal displays which are commonly used in portable computers.

Claim 30 is rejected under 35 U.S.C. 103(a) as being unpatentable over Ohtani et al., U.S. Patent 5,643,826 in view of Fukuda et al., U.S. Patent 6,096,585 as applied

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to claims 29, 31, and 33 above, and further in view of Zhang et al., U.S. Patent 5,403,772.

Both Ohtani et al. and Fukuda et al. are applied as above but fail to expressly disclose where the p-type region formation is conducted after the protective film is formed so that a p type region is formed in an offset form.

Zhang et al. discloses forming a p-type transistor with an offset due to the presence of the protective film on the gates which is an anodic oxide film (see figs. 10A-10C and col. 19-line 1 – col. 20-line 8). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the primary reference of Ohtani et al. so as to implant after formation of the anodic oxide protection film because this will reduce any implant damage to the gate electrode.

Claim 32 is rejected under 35 U.S.C. 103(a) as being unpatentable over Ohtani et al., U.S. Patent 5,643,826 in view of Fukuda et al., U.S. Patent 6,096,585 as applied to claims 29, 31, and 33 above, and further in view of Yamamoto et al., U.S. Patent 5,672,523.

Ohtani et al. and Fukuda et al. are applied as above but fail to expressly disclose the gate electrode formed of a heat resistant material specifically tantalum. Yamamoto et al. discloses making the gate electrode and gate bus lines of different materials, for example, the gate of tantalum and the bus lines of aluminum (see abstract). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the reference of Ohtani et al. so as to form the gate of

tantalum as taught by Yamamoto et al. because tantalum forms a better anodic oxide and is a better gate material than previously used materials (see col. 2-lines 1-62).

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Richard A. Booth whose telephone number is 308-3446. The examiner can normally be reached on Monday-Thursday from 7:30-6:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on 308-3325. The fax phone numbers for the organization where this application or proceeding is assigned are 308-7724 for regular communications and 308-7724 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 308-1782.

Richard A. Booth Primary Examiner Art Unit 2812